

IN THE SPECIFICATION

Please amend the paragraph at page 24, line 25 through page 25, line 6 to read as follows:

Recently, since the circuit of the semiconductor became finer, in order to form the fine circuit pattern more precisely, the process for averaging the surface of each layer formed on the wafer W has been employed. The representative process is CMP process (chemical and mechanical polishing process)[[,]] in which ~~polishing~~ the surface of the film formed ~~is~~ polished to flatten the coating surface. CMP process is sometimes applied [[on]] to the inter-layer insulating film (which is made of dielectric ~~objects~~ such as silicon dioxide) in the wiring layers (which is made of metals) of the semiconductor integrated circuit.

Please amend the paragraph at page 44, line 25 through page 45, line 6 to read as follows:

Fig. 12 is a flow chart showing an example of manufacturing a device (a semiconductor chip such as an IC, or LSI, a liquid crystal panel, a CCD, a thin film magnetic head, a micromachine, or the like). As shown in Fig. 12, in step 301 (design step), function/performance is designed for a device (e.g., circuit design for a semi conductor device) and a pattern to implement the function is designed. In step 302 (mask manufacturing step), a mask on which the designed circuit pattern is formed is manufactured. In step 303 (wafer manufacturing step), a wafer W is ~~manufacturing~~ manufactured by using ~~an object~~ a material such as silicon.